

**EAST Search History****EAST Search History (Prior Art)**

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	8014	(257/295-300,E21.649, E21.653.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 11:14
S2	44	("5371700" "5284799" "5644151" "5414655" "5789303" "5335138" "5880991" "5567636" "6249014" "5284799" "5672533" "6509601" "6455327" "6458604" "6509601" "6538272" "6555428" "6559003" "6613586" "5796133" "6313539" "6459111" "6429089").pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 12:36
S3	2	"6121648".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 11:35
S4	44	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/08 13:04
S5	5068	capacitor with sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 11:40
S6	14	S4 and S5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/08 13:05
S7	6	S6 and S1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/08 13:05

S8	764	S1 and S5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 11:40
S9	230	S1 and S5 and ((silicon adj oxide) same sidewall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 11:40
S10	2	"6441420".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 12:25
S11	4188	(contact adj plug) same (polysilicon or tungsten)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 12:25
S12	634	S11 and S1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 12:26
S13	18	S11 and S4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:45
S14	120	S11 and S1 and S5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 12:26
S15	8	("5371700" "5284799" "5644151" "5414655" "5789303" "5335138" "5880991" "5567636" "6249014" "5284799" "5672533" "6509601" "6455327" "6458604" "6509601" "6538272" "6555428" "6559003" "6613586" "5796133" "6313539" "6459111" "6429089").pn. and ((lead adj zirconate adj titanate) or (barium adj strontium adj titanate) or (tantalum adj pentoxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/26 15:37

S16	2	("5644151" "6121648").pn.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2007/07/26 15:38
S17	4	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier) and @pd>"20070326"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:46
S18	8494	(257/295-300,E21.649, E21.653.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/08 13:05
S19	48	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:46
S20	5262	capacitor with sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/08 13:05
S21	15	S19 and S20	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/08 13:05
S22	0	S21 and S18 and @pd>"20070326"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:47
S23	1	S19 and S20 and @pd>"20070326"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:47
S24	4470	(contact adj plug) same (polysilicon or tungsten)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/08 13:05
S25	2	S24 and S19 and @pd>"20070326"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:47

S26	4	S17 S23 S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:47
S27	49	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:45
S28	4601	(contact adj plug) same (polysilicon or tungsten)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:45
S29	0	S28 and S27 and @pd>"20070808"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:45
S30	1	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier) and @pd>"20070326" and @pd>"20070808"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:46
S31	1	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier) and @pd>"20070808"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:46
S32	49	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:47
S33	5359	capacitor with sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:47

S34	0	S32 and S33 and @pd>"20070326" and @pd>"20070808"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:47
S35	8623	(257/295-300,E21.649, E21.653.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:47
S36	15	S32 and S33	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:47
S37	0	S36 and S35 and @pd>"20070326" and @pd>"20070808"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:47
S38	0	S32 and S33 and @pd>"20070326" and @pd>"20070808"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:47
S39	4601 "	(contact adj plug) same (polysilicon or tungsten)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:47
S40	0	S39 and S32 and @pd>"20070326" and @pd>"20070808"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:47
S41	5	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier) and @pd>"20070326"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:48
S42	1	S32 and S33 and @pd>"20070326"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:48
S43	2	S39 and S32 and @pd>"20070326"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:48

S44	5	S41 S42 S43 and @pd>"20070808"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:48
S45	5	S30 S31 S42 S43 S44	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 14:48
S46	5	("6121648" "5644151"). pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 11:51
S47	11	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier) and @pd>"20070326" and @pd>"20070808"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/02 14:29
S48	11	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier) and @pd>"20070808"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/02 14:29
S49	59	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/02 14:29
S50	5698	capacitor with sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/02 14:29
S51	5215	(contact adj plug) same (polysilicon or tungsten)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/02 14:29

S52	15	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier) and @pd>"20070326"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/02 14:29
S53	4	S49 and S50 and @pd>"20070326"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/02 14:29
S54	7	S51 and S49 and @pd>"20070326"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/02 14:29
S55	15	S52 S53 S54 and @pd>"20070808"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/02 14:29
S56	15	S47 S48 S53 S54 S55	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/02 14:29
S57	9230	(257/295-300,E21.649, E21.653.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/02 14:29
S58	19	S49 and S50	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/02 14:29
S59	7	S58 and S57	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/02 14:29
S60	0	(insulating and film and field and effect and transistor and capacitor and contact and plug and hydrogen and barrier and different and materials and electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/02 15:18

S61	22	("5371700" "5284799" "5644151" "5414655" "5789303" "5335138" "5880991" "5567636" "6249014" "5284799" "5371700" "5672533" "6509601").pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/02 15:25
S62	5	("5371700" "5284799" "5644151" "5414655" "5789303" "5335138" "5880991" "5567636" "6249014" "5284799" "5371700" "5672533" "6509601").pn. and hydrogen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/02 15:27
S63	2	("5371700").pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/13 11:30
S64	0	(insulating and film and field and effect and transistor and capacitor and contact and plug and hydrogen and barrier and different and materials and electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/20 16:39
S65	65	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/20 16:39
S66	5885	capacitor with sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/20 16:39
S67	9463	(257/295-300,E21.649, E21.653.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/20 16:39
S68	20	S65 and S66	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/20 16:39

S69	8	S68 and S67	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/20 16:39
S70	20	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier) and @pd>"20070326" and @pd>"20070808"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:35
S71	20	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier) and @pd>"20070808"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:35
S72	68	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:35
S73	6121	capacitor with sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:35
S74	5967	(contact adj plug) same (polysilicon or tungsten)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:35
S75	24	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier) and @pd>"20070326"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:35
S76	6	S72 and S73 and @pd>"20070326"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:35

S77	11	S74 and S72 and @pd>"20070326"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:35
S78	24	S75 S76 S77 and @pd>"20070808"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:35
S79	24	S70 S71 S76 S77 S78	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:35
S80	10	S79 and @pd>"20080702"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:35
S81	20	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier) and @pd>"20070326" and @pd>"20070808"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:36
S82	20	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier) and @pd>"20070808"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:36
S83	68	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:36
S84	6121	capacitor with sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:36

S85	5967	(contact adj plug) same (polysilicon or tungsten)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:36
S86	24	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier) and @pd>"20070326"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:36
S87	6	S83 and S84 and @pd>"20070326"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:36
S88	11	S85 and S83 and @pd>"20070326"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:36
S89	24	S86 S87 S88 and @pd>"20070808"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:36
S90	24	S81 S82 S87 S88 S89	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:36
S91	10	S90 and @pd>"20080702"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:36
S92	68	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:36
S93	6121	capacitor with sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:36

S94	21	S92 and S93	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:36
S95	2	S94 and @pd>"20080702"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:36
S96	9826	(257/295-300,E21.649, E21.653.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:36
S97	9	S94 and S96	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:36
S98	2	S97 and @pd>"20080702"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:36
S99	0	(insulating and film and field and effect and transistor and capacitor and contact and plug and hydrogen and barrier and different and materials and electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/04 16:54
S100	33	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier) and @pd>"20070326" and @pd>"20070808"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35
S101	33	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier) and @pd>"20070808"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35

S102	80	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35
S103	6410	capacitor with sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35
S104	6466	(contact adj plug) same (polysilicon or tungsten)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35
S105	37	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier) and @pd>"20070326"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35
S106	9	S102 and S103 and @pd>"20070326"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35
S107	16	S104 and S102 and @pd>"20070326"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35
S108	37	S105 S106 S107 and @pd>"20070808"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35
S109	37	S100 S101 S106 S107 S108	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35

S110	33	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier) and @pd>"20070326" and @pd>"20070808"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35
S111	33	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier) and @pd>"20070808"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35
S112	80	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35
S113	6410	capacitor with sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35
S114	6466	(contact adj plug) same (polysilicon or tungsten)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35
S115	37	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier) and @pd>"20070326"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35
S116	9	S112 and S113 and @pd>"20070326"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35
S117	16	S114 and S112 and @pd>"20070326"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35

S118	37	S115 S116 S117 and @pd>"20070808"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35
S119	37	S110 S111 S116 S117 S118	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35
S120	80	(first with transistor) and (second with transistor) and capacitor and (upper adj electrode) and (lower adj electrode) and (metal adj oxide) and (hydrogen adj barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35
S121	6410	capacitor with sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35
S122	23	S120 and S121	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35
S123	10188	(257/295-300,E21.649, E21.653.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35
S124	10	S122 and S123	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:35
S125	0	(insulating and film and field and effect and transistor and capacitor and contact and plug and hydrogen and barrier and different and materials and electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:36
S126	51	S109 S119 S122 S124	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/26 10:43

2/26/10 10:57:11 AM

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